

# FDP6644/FDB6644

## 30V N-Channel PowerTrench® MOSFET

### General Description

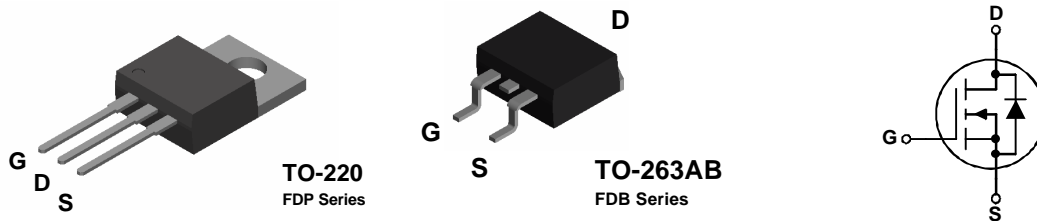
This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers.

These MOSFETs feature faster switching and lower gate charge than other MOSFETs with comparable  $R_{DS(ON)}$  specifications.

The result is a MOSFET that is easy and safer to drive (even at very high frequencies), and DC/DC power supply designs with higher overall efficiency.

### Features

- 50 A, 30 V.  $R_{DS(ON)} = 8.5 \text{ m}\Omega @ V_{GS} = 10 \text{ V}$   
 $R_{DS(ON)} = 10.5 \text{ m}\Omega @ V_{GS} = 4.5 \text{ V}$
- Low gate charge (27 nC typical)
- Fast switching speed
- High performance trench technology for extremely low  $R_{DS(ON)}$
- 175°C maximum junction temperature rating



### Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{DSS}$	Drain-Source Voltage	30	V
$V_{GSS}$	Gate-Source Voltage	$\pm 16$	V
$I_D$	Drain Current – Continuous (Note 1)	50	A
	– Pulsed (Note 1)	150	A
$P_D$	Total Power Dissipation @ $T_C = 25^\circ\text{C}$	83	W
	Derate above $25^\circ\text{C}$	0.55	W/ $^\circ\text{C}$
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-65 to +175	$^\circ\text{C}$

### Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	1.8	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	$^\circ\text{C/W}$

### Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDB6644	FDB6644	13"	24mm	800 units
FDP6644	FDP6644	Tube	n/a	45

**Electrical Characteristics** $T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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**Drain-Source Avalanche Ratings (Note 1)**

$W_{DSS}$	Single Pulse Drain-Source Avalanche Energy	$V_{DD} = 15\text{ V}, I_D = 25\text{ A}$			240	mJ
$I_{AR}$	Maximum Drain-Source Avalanche Current				25	A

**Off Characteristics**

$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$		26		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
$I_{GSSF}$	Gate-Body Leakage, Forward	$V_{GS} = 16\text{ V}, V_{DS} = 0\text{ V}$			100	NA
$I_{GSSR}$	Gate-Body Leakage, Reverse	$V_{GS} = -16\text{ V}, V_{DS} = 0\text{ V}$			-100	NA

**On Characteristics (Note 2)**

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	1	1.5	3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$		-5		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 25\text{ A}$ $V_{GS} = 4.5\text{ V}, I_D = 25\text{ A}$ $V_{GS} = 10\text{ V}, I_D = 25\text{ A}, T_J = 125^\circ\text{C}$		6.4 7.3 9.3	8.5 10.5 15	m $\Omega$
$I_{D(on)}$	On-State Drain Current	$V_{GS} = 10\text{ V}, V_{DS} = 5\text{ V}$	60			A
$g_{FS}$	Forward Transconductance	$V_{DS} = 5\text{ V}, I_D = 25\text{ A}$		98		S

**Dynamic Characteristics**

$C_{iss}$	Input Capacitance	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}$		3068		pF
$C_{oss}$	Output Capacitance	$f = 1.0\text{ MHz}$		513		pF
$C_{riss}$	Reverse Transfer Capacitance			196		pF

**Switching Characteristics (Note 2)**

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 15\text{ V}, I_D = 1\text{ A}$		12.5	22.5	ns
$t_r$	Turn-On Rise Time	$V_{GS} = 10\text{ V}, R_{GEN} = 6\ \Omega$		8	16	ns
$t_{d(off)}$	Turn-Off Delay Time			54	86	ns
$t_f$	Turn-Off Fall Time			14	26	ns
$Q_g$	Total Gate Charge	$V_{DS} = 15\text{ V}, I_D = 25\text{ A}$		27	38	nC
$Q_{gs}$	Gate-Source Charge	$V_{GS} = 4.5\text{ V}$		9		nC
$Q_{gd}$	Gate-Drain Charge			7		nC

**Drain-Source Diode Characteristics and Maximum Ratings**

$I_S$	Maximum Continuous Drain-Source Diode Forward Current				50	A
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 25\text{ A}$ (Note 2)		0.8	1.3	V

**Notes:**

1. Calculated continuous current based on maximum allowable junction temperature. Actual maximum continuous current limited by package constraints to 75A.
2. Pulse Test: Pulse Width < 300 $\mu\text{s}$ , Duty Cycle < 2.0%

### Typical Characteristics

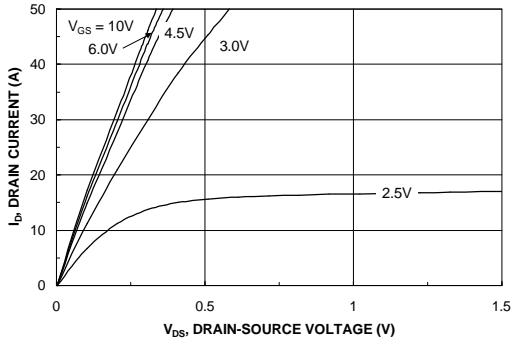


Figure 1. On-Region Characteristics.

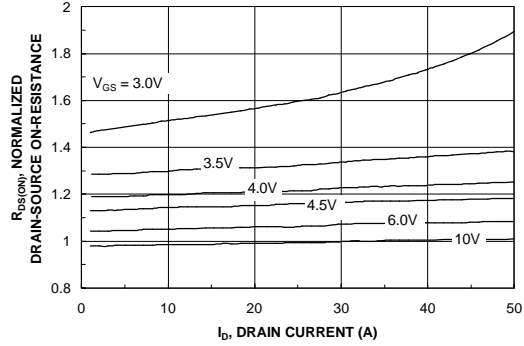


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

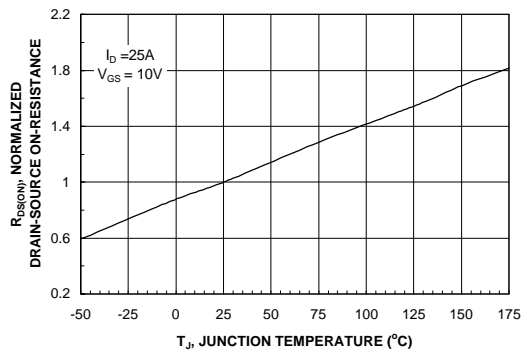


Figure 3. On-Resistance Variation with Temperature.

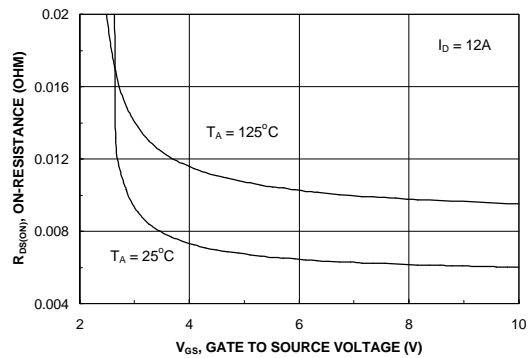


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

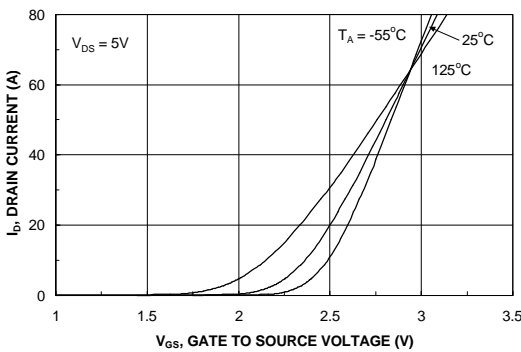


Figure 5. Transfer Characteristics.

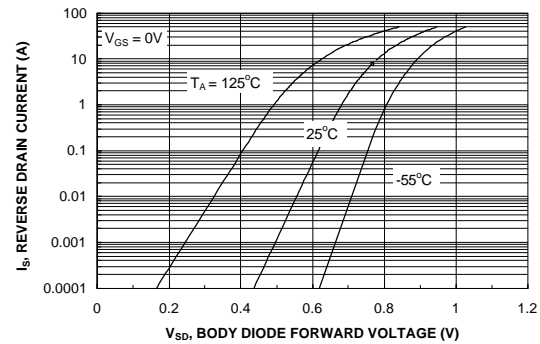


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

## Typical Characteristics

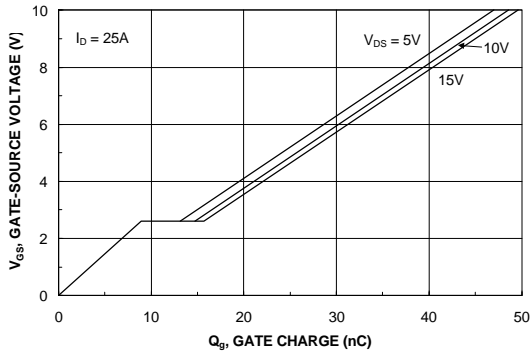


Figure 7. Gate Charge Characteristics.

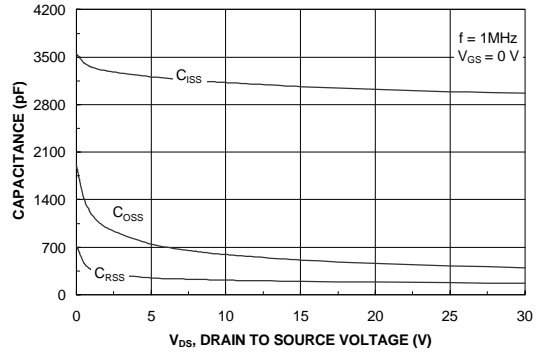


Figure 8. Capacitance Characteristics.

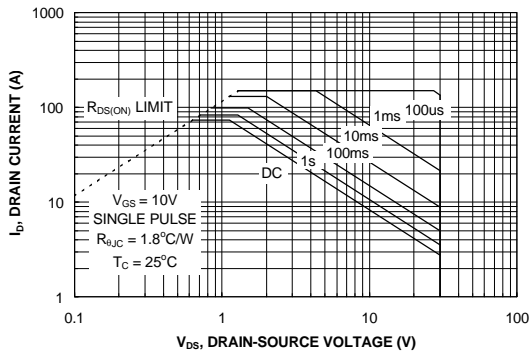


Figure 9. Maximum Safe Operating Area.

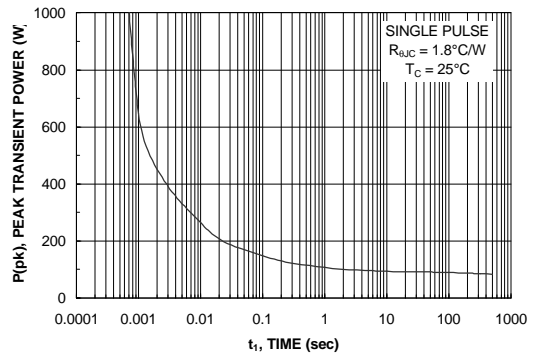


Figure 10. Single Pulse Maximum Power Dissipation.

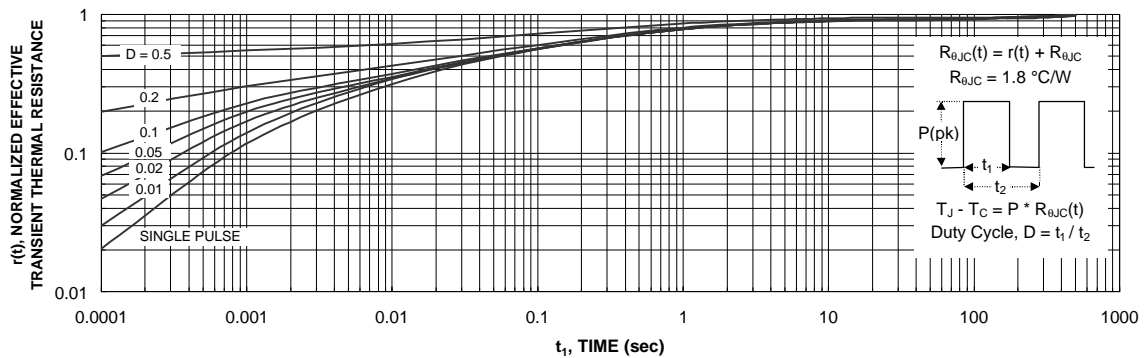


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1.  
Transient thermal response will change depending on the circuit board design.

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